



Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C		
20V	42mΩ @ V _{GS} = 10V	3.5A		
201	45mΩ @ V _{GS} = 4.5V	3.3A		

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- **Power Management Functions**
- Backlighting

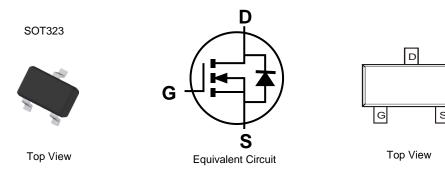
N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.006 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2058UW-7	SOT323	3000/Tape & Reel
DMN2058UW-13	SOT323	10000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. Notes:

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

58U	ΥM

58U= Product Type Marking Code YM or \overline{YM} = Date Code Marking for SAT Y or \overline{Y} = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

	Cy											
Year	20	17	2018	2019	202	0	2021	2022	2023	20)24	2025
Code			F	G	Н			J	K		L	М
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	20	V	
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	3.5 3.0	А
Maximum Continuous Body Diode Forward Currer	nt (Note 6)	Is	1.0	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	I _{DM}	20	А		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.5	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	259	°C/W
Total Power Dissipation (Note 6)		PD	0.7	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	175	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

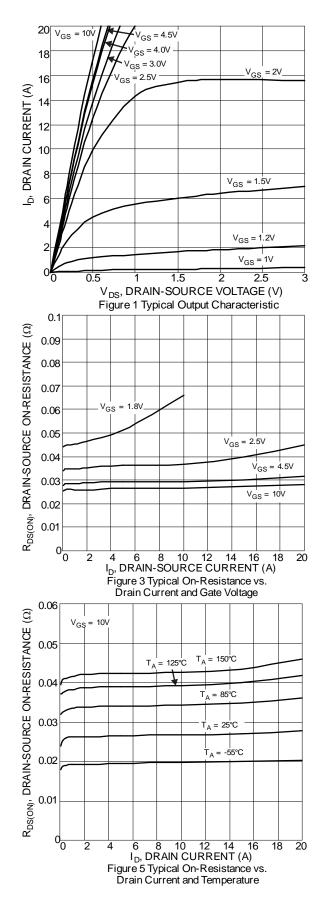
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)			•			
Gate Threshold Voltage	V _{GS(TH)}	0.4	—	1.2	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
			31.5	42		$V_{GS} = 10V, I_D = 3A$
Static Drain-Source On-Resistance	D		32	45	mΩ	$V_{GS} = 4.5V, I_D = 2A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	40.5	60	mΩ	$V_{GS} = 2.5V, I_D = 2A$
			48	91		V _{GS} = 1.8V, I _D = 1A
Diode Forward Voltage	V _{SD}	_	0.78	1.2	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 8)				•	•	
Input Capacitance	C _{iss}	_	281	_	pF	
Output Capacitance	Coss	_	50	_	pF	−V _{DS} = 10V, V _{GS} = 0V −f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	—	39	_	pF	
Gate Resistance	Rg	_	3.1	_	Ω	$f = 1.0MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	3.6	—	nC	
Total Gate Charge (V _{GS} = 10V)	Qq	—	7.7	—	nC	
Gate-Source Charge	Q _{gs}	_	0.5	—	nC	$V_{DS} = 10V, I_D = 6.0A$
Gate-Drain Charge	Q _{qd}	—	0.9	—	nC	
Turn-On Delay Time	t _{D(ON)}	_	2.0	—	ns	
Turn-On Rise Time	t _R	_	4.9	—	ns	$V_{GS} = 4.5V, V_{DD} = 10V, R_g = 6\Omega,$
Turn-Off Delay Time	t _{D(OFF)}	_	9.9	—	ns	$I_{\rm D} = 6.0{\rm A}$
Turn-Off Fall Time	t _F	_	3.3	—	ns	1
Body Diode Reverse Recovery Time	t _{RR}	_	5.4	_	ns	I _F = 6.0A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	_	0.7	_	nC	I _F = 6.0A, di/dt = 100A/µs

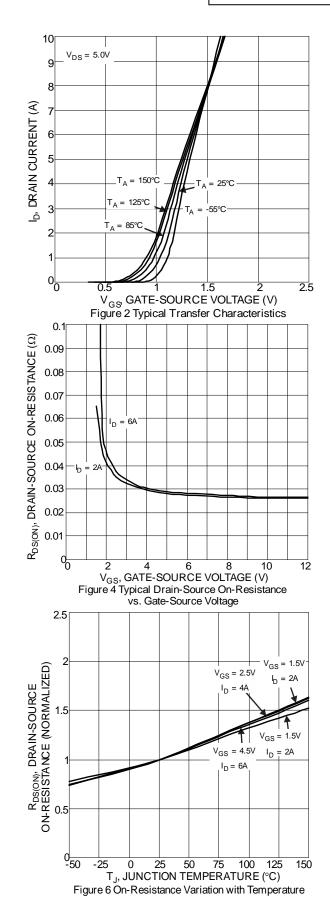
Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout.
 Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

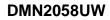


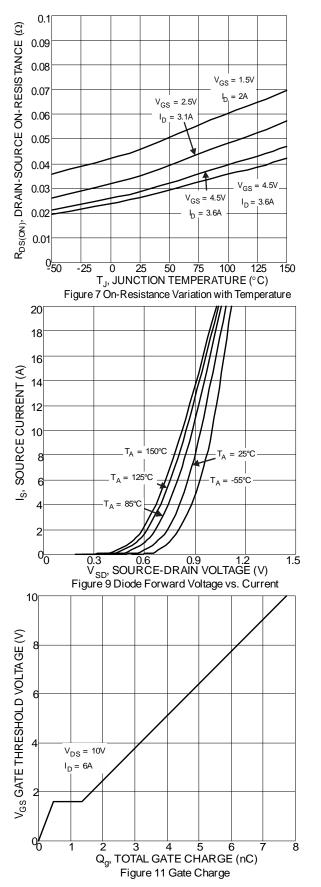
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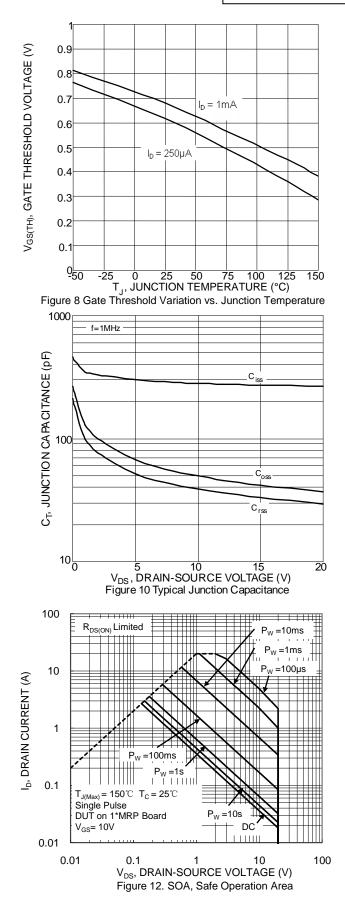




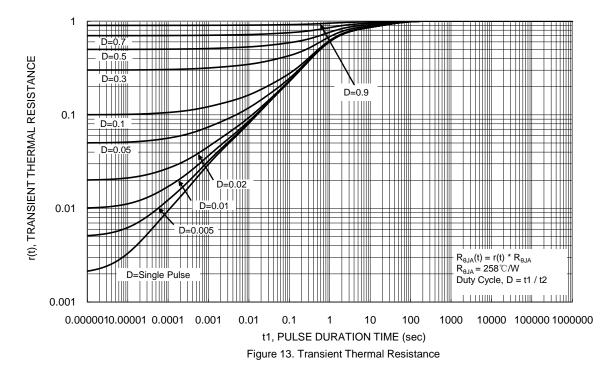








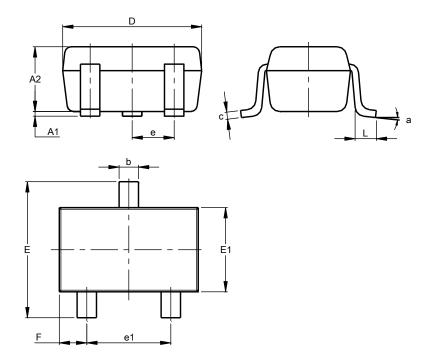






Package Outline Dimensions

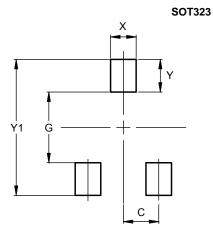
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
c	0.10	0.18	0.11				
D	1.80	2.20	2.15				
ш	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C).650 B	SC				
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All	Dimen	sions i	in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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